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Preparation and characteristics of SnS₂ saturable absorber and its application in passively Q-switched Nd:YAG/Cr⁴⁺:YAG laser

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ABSTRACT

In this paper, the preparation and characteristics of SnS₂ saturable absorber were demonstrated, and the SnS₂ saturable absorber was used in Nd:YAG/Cr⁴⁺:YAG laser. Under different output coupler, repetition rate showed the range from 1.5 kHz to 6.2 kHz and pulse width showed the range from 3.1 ns to 5.8 ns with the increasing pump power. The max pulse energy was 29 μJ with peak power of 9.4 kW.

1. Introduction

Passively Q-switched (PQS) operation provides lower output performances compared to active Q-switched (AQS), but it shows more advantages like simple cavity structure, lower costs and reliability. The PQS technique, generated laser pulse width less than microsecond, is of great significance for scientific research, military applications, materials processing, medical examination and remote sensing [1–4]. In PQS lasers, the saturable absorbers (SAs) are recognized as the key device. In recent decades, the SAs had experienced a long process of development. For example: dyes, crystals such as Cr⁴⁺:YAG [5], Cr²⁺:ZnSe [6,7], SESAM/SBR-based nonlinear mirrors [8,9] and graphene or graphene-like materials. Among these saturable absorber (SA) materials, Cr⁴⁺:YAG crystals, with excellent heat conductivity, stable optical property and heat conductivity, have been employed for LD-pumped composite crystal lasers [10,11]. Generally, Cr⁴⁺:YAG laser could not generate high peak power pulses.

In order to develop highly compact laser system, we combined the gain medium and the SA. Nd:YAG/Cr⁴⁺:YAG composite crystal with thin pieces of Nd:YAG bonded to thin pieces of Cr⁴⁺:YAG by using diffusion composite technique, is widely used to fabricate micro compact PQS lasers with infrared output [12]. On one hand, compared to the co-doped Nd:YAG laser media and the Cr⁴⁺:YAG single crystal lasers, composite crystals have the advantages such as rather slight thermal effects of active medium and compact laser cavity [13]. On the other hand, with the same Cr⁴⁺:YAG crystal and cavity, the pulse width in Nd:YAG/Cr⁴⁺:YAG composite crystal exhibited shorter [13,14]. Therefore, the composite crystal could be recognized as an ideal laser material with some advantages such as: low thermal lens effect by the end face deformation, high light-to-light conversion efficiency and damage threshold, good output beam quality and compact laser cavity.

Among the transition metal sulfides (TMDs) layered materials, SnS₂ exhibits excellent photoelectric properties such as deeper modulation depth than graphene and wider modulation wavelength range than MoS₂ and WS₂ [15–22]. These properties make SnS₂ a good candidate as the SA in lasers, but there are still few reports about the SnS₂ SA used in composite crystal lasers. In order to obtain shorter pulse width and highly stable PQS operation, the SnS₂ SA and the Nd:YAG/Cr⁴⁺:YAG composite crystal were combined in

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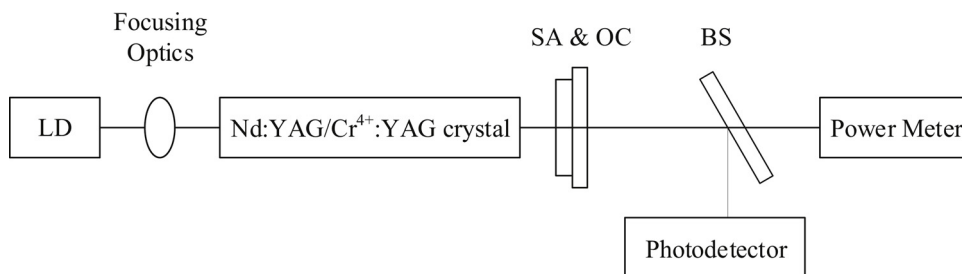


Fig. 1. Experimental setup of the PQS Nd:YAG/Cr⁴⁺:YAG laser.

laser cavity.

In this paper, the preparation and characteristics of SnS₂ SA were demonstrated, and the SnS₂ SA was used in PQS Nd:YAG/Cr⁴⁺:YAG laser. Typical pulse profile and beam profile of the PQS Nd:YAG/Cr⁴⁺:YAG laser were also demonstrated. Moreover, the SnS₂ SA-based solid-state laser is reported for the first time [23,24].

2. Experimental setup

The experimental setup of the PQS Nd:YAG/Cr⁴⁺:YAG laser was shown in Fig. 1. The central wavelength of fiber-coupled laser diode was 808 nm, and the max output power was 3 W. The beam spot radius was 200 μm with numerical aperture of 0.22. The cavity length of 14 mm was designed. The input side was a 1.1 % doped Nd:YAG with the dimensions of 3 × 3 × 5 mm³, and the other side was a 3 × 3 × 2 mm³ Cr⁴⁺:YAG crystal with an initial transmission of 65 %. The crystal was HT-coated at 808 nm and HR-coated at 1064 nm on input side, and AR-coated at 1064 nm on the other side. The SnS₂ SA was employed. The composite crystal was cooled by TEC at the temperature of 28 °C. The output couplers (OCs) were flat mirrors with 1.5 %, 3%, 10 % and 27 % transmission at 1.06 μm. The temporal pulse profile was recorded by a digital oscilloscope (Agilent DSO7012B) and an InGaAs photodetector (Thorlabs PDA015C). The output power was measured by a power meter (Thorlabs PM100D).

3. Experimental results and discussions

3.1. Preparation and characterization of SnS₂ SA

The fabricating method of SnS₂ SA was liquid-phase stripping and demonstrated as follows: At first, 0.1 g of SnS₂ powder with diameter less than 10 μm was added into 25 ml analytical pure alcohol. Next, the solution was put in an ultrasonic machine for 10 h. After that, stirred the solution for 20 min with rotation rate of 1000 rpm. Then, got the supernatant liquid and dropped it on K9 substrate. Finally, left the substrate at 23°C for half a day.

The characterization of SnS₂ SA was demonstrated in Fig. 2. As shown in Fig. 2(a) and (b), SnS₂ SA showed a broad transmission range from 700 nm to 1100 nm. The linear transmission and linear absorption coefficient at 1064 nm are 83.8 % and 0.0767, respectively.

The nonlinear absorption property of the SnS₂ SA was demonstrated in Fig. 2(c). The femtosecond laser with 150 fs pulse width, central wavelength at 1040 nm and the repetition rate of 32 MHz was used. The saturation intensity was 153.2 MW/cm² and the modulation depth was 7.9 %. In Fig. 2(d), Raman spectroscopy of the SnS₂ SA was shown. Two typical peaks at 205 cm⁻¹ and 314 cm⁻¹ are related to the E_g and A_{1g}¹ vibrational modes. The AFM photograph and SEM photograph were shown in Fig. 2(e) and (f), the diameter and thickness of the SnS₂ SA were 300 nm and 5.72 nm (5 layers), respectively.

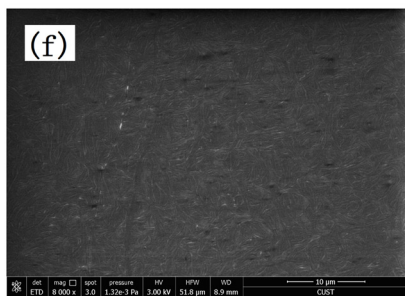
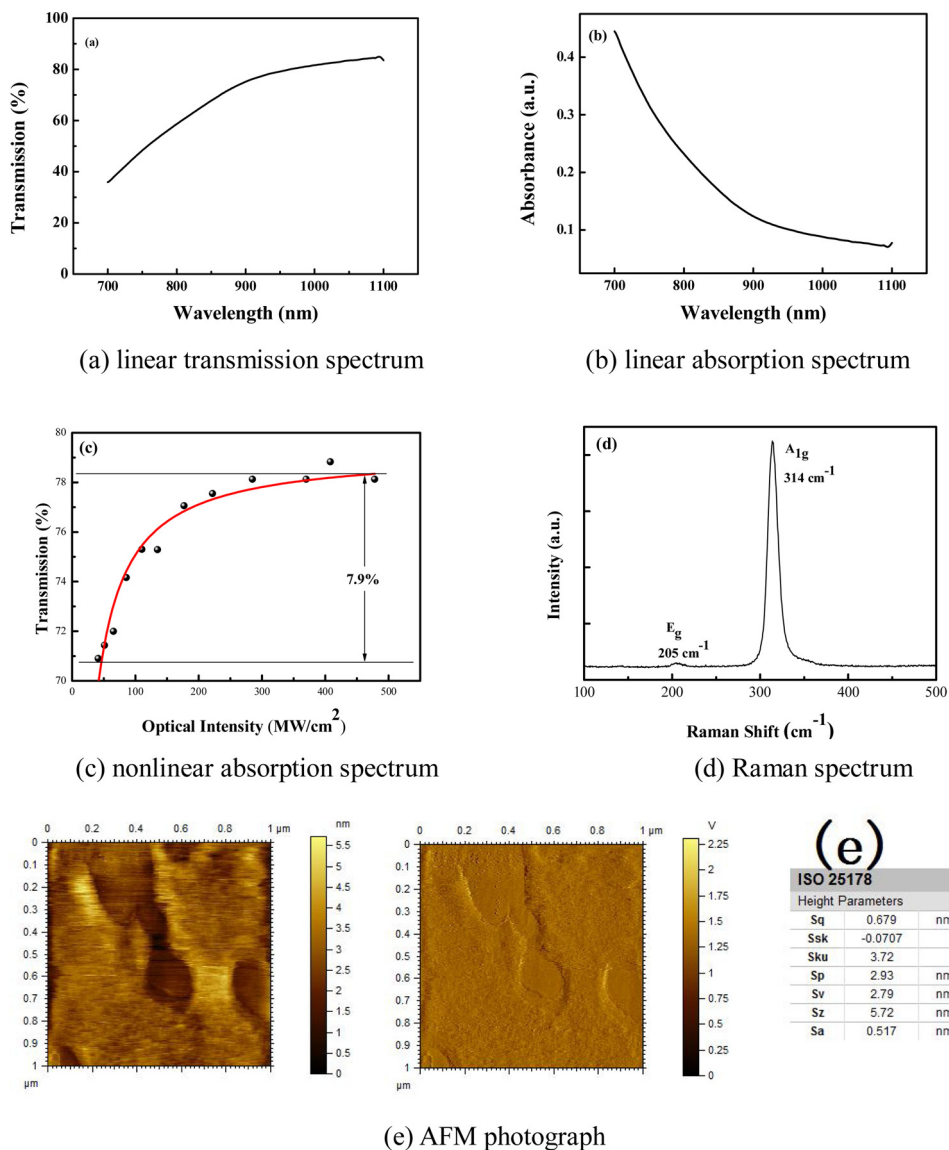
3.2. PQS Nd:YAG/Cr⁴⁺:YAG laser

The stable PQS Nd:YAG/Cr⁴⁺:YAG laser with SnS₂ SA was observed, and OCs with transmission of T = 1.5 %, 3%, 10 % and 27 % at 1064 nm were used.

Fig. 3 showed the relationship between output power and pump power at different output coupler (OC). With the increasing OC from 1.5% to 27%, the threshold pump power increased from 2.08 W to 2.22 W. Under pump power of 2.58 W: with the increasing OC from 1.5% to 27%, the output power increased from 22 mW to 180 mW, and the optical conversion efficiency increased from 0.85 % to 6.98 %.

Fig. 4 showed the variation of pulse width (PW) and repetition rate (RR) with increasing pump power at different OC. Under pump power of 2.58 W: with the increasing OC from 1.5% to 27%, the PW decreased from 4.4 ns to 3.1 ns, and the RR increased from 4.9 kHz to 6.2 kHz. Under pump power of 2.58 W and 27 % OC, the maximum pulse energy of 29 μJ with highest peak power of 9.4 kW was obtained.

Fig. 5 showed the pulse profile and beam profile of the PQS operation with 27 % OC. The far-field beam profile was shown in Fig.6(c), and the 808 nm pump laser oscillates at the fundamental transverse mode.



(f) SEM photograph

Fig. 2. Characterization of SnS₂ SA.

4. Conclusion

Based on the preparation and characteristics of the SnS₂ SA, a compact PQS Nd:YAG/Cr⁴⁺:YAG laser have been demonstrated. With pump power of 2.58 W and 27 % OC: the output power was 180 mW with optical-optical conversion efficiency of 6.98 %, the

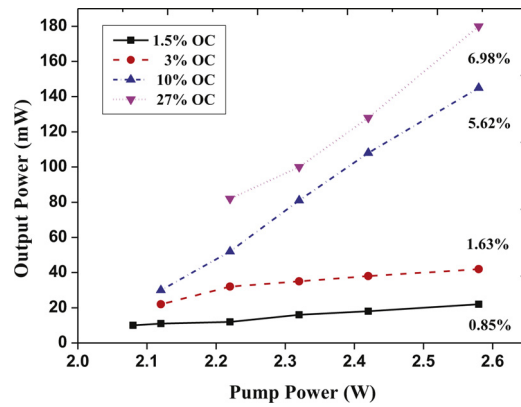


Fig. 3. Relationship between output power and pump power at different output coupler.

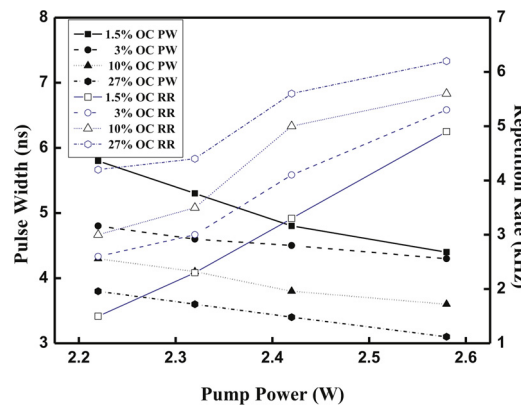
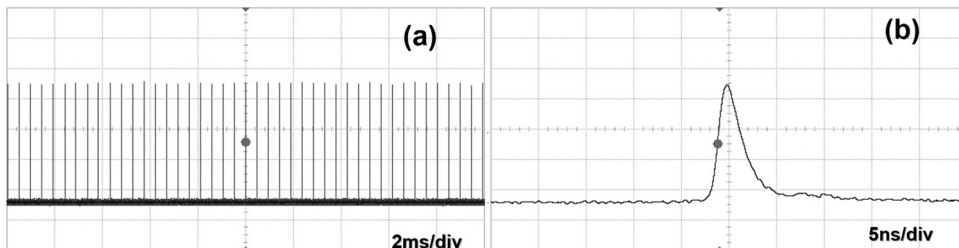
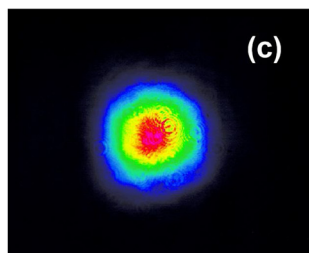


Fig. 4. Variation of pulse width and repetition rate with increasing pump power at different OC.



(a) Pulse trains

(b) Typical pulse profile



(c) typical beam profile

Fig. 5. Pulse profile and beam profile of the PQS operation with 27 % OC.

PW was 3.1 ns with RR of 6.2 kHz, and the single pulse energy of 29 μ J with peak power of 9.4 kW.

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Declaration of Competing Interest

The authors declare no conflict of interest.

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